PCN Number: 2024				240327001.2			PCN Date:			March 28, 2024	
Title: Qualification of RFAB using qualified Process Technology, Die Revision, and additional Assembly/Test site options									Revision, and		
Customer Contact:				Change Management team			Dept:			Quality Services	
Proposed 1 st Ship Date:				September 24, Estin 2024			mated Sample Availability:		•	April 27, 2024*	
*Sa	mple r	equests rece	ived a	afte	r April 27, 202	4 will n	ot b	e s	supporte	ed.	
Cha	inge Ty	ре:									
\boxtimes	Assem	bly Site			Design				Wafer I	Bump Material	
\boxtimes	Assem	bly Process			Data Sheet				Wafer Bump Process		
	Assem	bly Materials			Part number change			\boxtimes	Wafer Fab Site		
Mechanical Specification			tion		Test Site			\boxtimes	Wafer Fab Materials		
Packing/Shipping/ Labeling					Test Process				Wafer I	Fab Process	

PCN Details

Description of Change:

Texas Instruments is pleased to announce the addition of RFAB using the LBC9 qualified process technology and additional Assembly/Test site (CDAT, TIPI) options for the device listed below.

C	urrent Fab Si	te	Additional Fab Site			
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
DL-LIN	LBC3S	150 mm	RFAB	LBC9	300 mm	

The die was also changed as a result of the process change.

Additionally, there will be a BOM options introduced for these devices:

Group 1 Device BOM table:

	TIPI (Current)	TIPI (New)	CDAT
Bond wire composition, diameter	1.0 mil Cu	0.8 mil Cu	0.8mil Cu
Pin 1 Marking	Stripe	Dot	Dot
Lead finish	NiPdAu	NiPdAu or Matte Sn	Matte Sn
Final Wafer Thickness	267 um	152um	152um
Final Test site	TIPI	TIPI	CDAT
Probe Site	DL-MOS-4	CD-PR	CD-PR

Group 2 Device BOM table:

•	LEN	TIPI	CDAT
Bond wire composition,			
diameter	1.0mil Au	0.8 mil Cu	0.8mil Cu
Pin 1 Marking	Stripe	dot	Dot
Lead finish	NiPdAu	NiPdAu or Matte Sn	Matte Sn
Final Wafer Thickness	267um	152 um	152um
Final Test site	LEN	TIPI	CDAT
Probe Site	DL-MOS-4	CD-PR	CD-PR

Test coverage, insertions, conditions will remain consistent with current testing.

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring

our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	No Change	No Change	No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
RFAB	RFB	USA	Richardson

Die Rev:

Current	New
Die Rev [2P]	Die Rev [2P]
RΛ	Λ.

Assembly/Test Site

Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City		
LEN	LIN	TWN	Taichung		
TIPI	PHI	PHL	Baguio City		
CDAT	CDA	CHN	Chengdu		

Sample product shipping label (not actual product label)



CTTEM: 1750 LBL: 5A (L)TO:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY(1T) 7523483S12 (P) REV: (V) 6033917 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

Group 1 Device list:

SN381WDDBVRQ1 TPS3813K33QDBVRAL TPS3813K33QDBVRQ1 TPS3813I50QDBVRQ1

Group 2 Device list:

TPS3813K33QDBVRCT2

For alternate parts with similar or improved performance, please visit the product page on II.com

Automotive Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

TPS3813Q1 Automotive Qualification LBC9-RFAB, DBV6-PHI Approve Date 01-March-2024

Product Attributes

Attributes	Qual Device:	QBS Process Reference:	QBS Package, Process, Product Reference:		
Attributes	TPS3813K33QDBVRQ1	BQ79600PWRQ1	PTPS3840PHXXDBVR		
Automotive Grade Level	Grade 1	Grade 1	Grade 1		
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125		
Product Function	Power Management	Power Management	Power Management		
Wafer Fab Supplier	RFAB	RFAB	RFAB		
Assembly Site	PHI	MLA	PHI		
Package Group	SOT	TSSOP	SOT		
Package Designator	DBV	PW	DBV		
Pin Count	6	16	5		

- QBS: Qual By Similarity
- Qual Device TPS3813K33QDBVRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot	SS /	Test Name	Condition	Duration	Qual Device:	QBS Process Reference:	QBS Package, Process, Product Reference:
			Qty					TPS3813K33QDBVRQ1	BQ79600PWRQ1	PTPS3840PHXXDBVR
Test Group	A - Acc	elerated Environ	ment St	ress Tes	its					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	-	1/0/0	-	3/0/0
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-		3/0/0	
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
AC/UHAST	АЗ	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-
AC/UHAST	АЗ	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0		3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/77/0	3/135/0	3/135/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS3813K33QDBVRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Package, Process, Product Reference: PTPS3840PHXXDBVR
Test Group I	B - Acce	lerated Lifetime	Simula	tion Test	s					
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	3/231/0
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
EDR	В3	AEC Q100- 005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS-009- 018	1 Step	-	3/231/0	-
Test Group	C - Pack	age Assembly I	ntegrity	Tests						
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
SD	С3	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	1/15/0
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0
Test Group I	D - Die F	abrication Relia	bility Te	sts						
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS3813K33QDBVRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Package, Process, Product Reference: <u>PTPS3840PHXXDBVR</u>
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
ВТІ	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verification	n Tests							
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	-	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	-	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	2/60/0	3/90/0
Additional T	ests									

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2301-019

TI Information Selective Disclosure

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at PHI Approve Date 01-March-2024

Attributes	Qual Device: <u>TPS3813K33QDBVRQ1</u>	QBS Process Reference: <u>BQ79600PWRQ1</u>	QBS Package, Process, Product Reference: PTPS3840PHXXDBVR
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	PHI	MLA	РНІ
Package Group	SOT	TSSOP	SOT
Package Designator	DBV	PW	DBV
Pin Count	6	16	5

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS3813K33QDBVRQ1	QBS Reference: BQ79600PWRQ1	QBS Reference: PTPS3840PHXXDBVR
Test G	roup A - A	Accelerated En	vironme	nt Stres	s Tests					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	-	-	-	3/0/0
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	-	3/0/0	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	-	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	-	-	3/66/0
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	-	-	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	-	-	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	-	-	3/9/0
HAST	A2.2	JEDEC JESD22- A110	3	70	Biased HAST	130C/85%RH	192 Hours	-	3/210/0	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	3/66/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS3813K33QDBVRQ1	QBS Reference: BQ79600PWRQ1	QBS Reference: PTPS3840PHXXDBVR
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	-	3/9/0	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	-	3/9/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	-	3/9/0	3/9/0
TC	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	3/66/0	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-	3/3/0
тс	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	-	-	3/9/0
тс	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	-	-	3/9/0
тс	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	-	-	3/9/0
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	-	3/210/0	3/231/0
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	3/66/0	3/66/0
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS3813K33QDBVRQ1	QBS Reference: BQ79600PWRQ1	QBS Reference: PTPS3840PHXXDBVR
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	-	3/9/0	3/9/0
тс	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	-	3/9/0	3/9/0
тс	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	-	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-	3/3/0
HTSL	A6.2	JEDEC JESD22- A103	3	44	High Temperature Storage Life	150C	2000 Hours	-	3/132/0	3/135/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0
Test G	roup C - F	Package Assen	nbly Inte	grity Tes	sts					
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0

- · QBS: Qual By Similarity
- Qual Device TPS3813K33QDBVRQ1 is qualified at MSL1 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2301-019

Automotive Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

TPS3813Q1 Automotive Qualification LBC9-RFAB, DBV6-CDAT Approve Date 01-March-2024

Product Attributes

Attributes	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:	
Attributes	TPS3813K33QDBVRQ1	BQ79600PWRQ1	TPS3840PH30DBVRQ1	TPS3813K33QDBVRQ1	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	
Product Function	Power Management	Power Management	Power Management	Power Management	
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	
Assembly Site	CDAT	MLA	CDAT	PHI	
Package Group	SOT	TSSOP	SOT	SOT	
Package Designator	DBV	PW	DBV	DBV	
Pin Count	6	16	5	6	

- QBS: Qual By Similarity
 Qual Device TPS3813K33QDBVRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min	SS /	Test Name	Condition	Duration	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:
			Qty	1.31-0277				TPS3813K33QDBVRQ1	BQ79600PWRQ1	TPS3840PH30DBVRQ1	TPS3813K33QDBVRQ1
Test Group	A - Acc	elerated Enviror	ment S	tress Te	sts						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	2	1/0/0		3/0/0	1/0/0
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C			3/0/0		
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	
AC/UHAST	АЗ	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	3/231/0	-
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0			1/77/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0	3/231/0	1/77/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-		1/5/0	-	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/77/0	3/135/0	3/135/0	1/77/0
Test Group	B - Acc	elerated Lifetime	e Simula	tion Tes	its			155		20	
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	3/231/0	-
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours		3/2400/0		
EDR	В3	AEC Q100- 005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS-009- 018	1 Step		3/231/0	-	-

Туре	#	Test Spec	Min Lot	SSI	Test Name	Condition	Duration	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:
			Qty	Lot				TPS3813K33QDBVRQ1	BQ79600PWRQ1	TPS3840PH30DBVRQ1	TPS3813K33QDBVRQ1
Test Grou	p C - Pac	kage Assembly	Integrity	Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	1/15/0	
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage		-	1/15/0	1/15/0	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0	1/10/0
Test Grou	p D - Die	Fabrication Relia	ability Te	sts	<i>a</i> .						
ЕМ	D1	JESD61			Electromigration			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35			Time Dependent Dielectric Breakdown			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28			Hot Carrier Injection			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
ВТІ	D4				Bias Temperature Instability			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-			Stress Migration	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Type	#	Test Spec	Min	ss i	Test Name	Condition	Duration	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:
			Qty	Lot				TPS3813K33QDBVRQ1	BQ79600PWRQ1	TPS3840PH30DBVRQ1	TPS3813K33QDBVRQ1
ESD	E2	AEC Q100- 002	1	3	ESD HBM		2000 Volts	-	-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts		-		1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-				1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold			2/60/0	3/90/0	3/90/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

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 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

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- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
 Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- · Room : AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2301-020

ZVEI ID: SEM-DE-03, SEM-PW-02, SEM-PW-03, SEM-PW-09, SEM-PW-13, SEM-PA-05, SEM-PA-08, SEM-PA-13, SEM-PA-18, SEM-PS-04, SEM-TF-01

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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